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- Members of the Texas Instruments Widebus™ Family
- B-Port Outputs Have Equivalent 25-Ω
 Series Resistors, So No External Resistors
 Are Required
- State-of-the-Art EPIC-IIB™ BiCMOS Design Significantly Reduces Power Dissipation
- UBT™ (Universal Bus Transceiver)
 Combines D-Type Latches and D-Type
 Flip-Flops for Operation in Transparent,
 Latched, or Clocked Mode
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 5 V, T_A = 25°C
- High-Impedance State During Power Up and Power Down
- Flow-Through Architecture Optimizes PCB Layout
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Shrink Small-Outline (DL) Package and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

description

These 18-bit universal bus transceivers combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes. Data flow in each direction is controlled by output-enable (OEAB and OEBA), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs.

SN54ABT162500 . . . WD PACKAGE SN74ABT162500 . . . DL PACKAGE (TOP VIEW)

			U			
OEAB	п	l .	$\overline{}$			GND
LEAB	q	2		55	0	CLKAB
A1	q	3		54		B1
GND	q	4		53	1	GND
A2	q	5		52	P	B2
A3	\neg	6		51	P	B3
V_{CC}	Q	7		50		
A4				49	1	B4
A5	q	9		48	0	B5
A6				47	þ	B6
GND				46	þ	GND
A7	q	12		45	þ	B7
A8	\neg	13		44		B8
A9	Q	14		43	þ	B9
A10	q	15		42	þ	B10
A11	q	16		41	þ	B11
A12	q	17		40		B12
GND	q	18		39	þ	GND
A13	q	19		38	þ	B13
A14	q	20		37	1	B14
A15	Q	21		36	þ	B15
V_{CC}	q	22		35	þ	V_{CC}
A16	q	23		34	1	B16
A17	Q	24		33	þ	B17
GND	q	25		32	þ	GND
A18	D	26		31		B18
OEBA	D	27		30		CLKBA
LEBA	q	28		29		GND

For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the high-to-low transition of CLKAB. Output-enable OEAB is active high. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{\text{OEBA}}$, LEBA, and $\overline{\text{CLKBA}}$. The output enables are complementary (OEAB is active high and $\overline{\text{OEBA}}$ is active low).

The B-port outputs, which are designed to source or sink up to 12 mA, include equivalent 25- Ω series resistors to reduce overshoot and undershoot.



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description (continued)

When V_{CC} is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, \overline{OE} should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

The SN54ABT162500 is characterized for operation over the full military temperature range of -55° C to 125°C. The SN74ABT162500 is characterized for operation from -40° C to 85°C.

FUNCTION TABLE†

	INPUTS							
OEAB	LEAB	CLKAB	Α	В				
L	Х	Х	Х	Z				
Н	Н	Χ	L	L				
Н	Н	Χ	Н	Н				
Н	L	\downarrow	L	L				
Н	L	\downarrow	Н	Н				
Н	L	Н	Χ	в ₀ ‡ в ₀ §				
Н	L	L	Χ	В ₀ §				

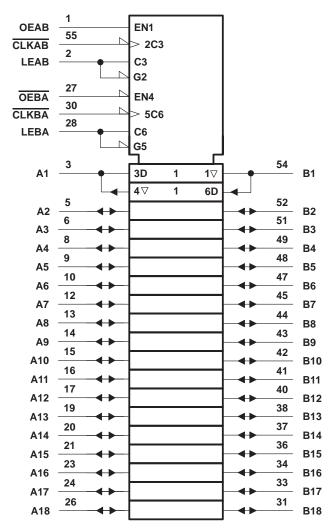
[†] A-to-B data flow is shown: B-to-A flow is similar but uses OEBA, LEBA, and CLKBA.

[‡]Output level before the indicated steady-state input conditions were established

[§] Output level before the indicated steady-state input conditions were established, provided that CLKAB was low before LEAB went low

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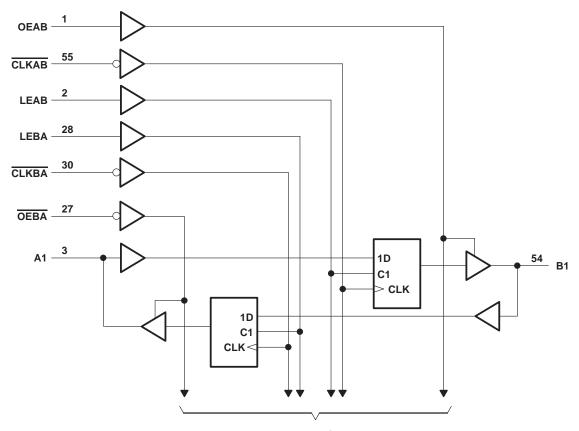
logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

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logic diagram (positive logic)



To 17 Other Channels

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	-0.5 V to 7 V
Input voltage range, V _I (except I/O ports) (see Note 1)	
Voltage range applied to any output in the high or power-off state, VO	
Current into any output in the low state, IO: SN54ABT162500 (A port)	96 mA
SN74ABT162500 (A port)	128 mA
B port	30 mA
Input clamp current, I _{IK} (V _I < 0)	–18 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Package thermal impedance, θ _{JA} (see Note 2): DL package	74°C/W
Storage temperature range, T _{stq}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.



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recommended operating conditions (see Note 3)

				162500	SN74ABT	UNIT	
			MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage	4.5	5.5	4.5	5.5	V	
VIH	High-level input voltage		2		2		V
V _{IL}	Low-level input voltage		0.8		0.8	V	
VI	Input voltage	0	Vcc	0	Vcc	V	
la	Lich level cutout current	A port	,	- 24		-32	mA
ТОН	High-level output current B port		<i>\(\frac{1}{2} \)</i>	-12		-12	IIIA
la.	Laurent autout autout	A port	25	48		64	Λ
IOL	Low-level output current	B port	000	12		12	mA
Δt/Δν	Input transition rise or fall rate	Outputs enabled	Q,	10		10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200		200		μs/V
TA	Operating free-air temperature	-55	125	-40	85	°C	

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T	A = 25°C	;	SN54ABT	162500	SN74ABT162500		UNIT	
PA	RAMETER	I IEST CO	NUTTIONS	MIN	TYP [†]	MAX	MIN	MAX	MIN	MAX	UNII	
VIK		V _{CC} = 4.5 V,	I _I = -18 mA			-1.2		-1.2		-1.2	V	
		$V_{CC} = 4.5 \text{ V},$	I _{OH} = -3 mA	2.5			2.5		2.5			
1	A ====	V _{CC} = 5 V,	I _{OH} = -3 mA	3			3		3			
1	A port	Van 45V	I _{OH} = -24 mA	2			2					
		V _{CC} = 4.5 V	I _{OH} = -32 mA	2*					2		V	
VOH		V _{CC} = 4.5 V,	I _{OH} = -1 mA	3.35			3.3		3.35		V	
	P port	V _{CC} = 5 V,	I _{OH} = -1 mA	3.85			3.8		3.85			
1	B port	V _{CC} = 4.5 V	I _{OH} = -3 mA	3.1			3		3.1			
		vCC = 4.5 v	I _{OH} = -12 mA	2.6					2.6			
	A port	V _{CC} = 4.5 V	I _{OL} = 48 mA			0.55		0.55				
VOL	A port	VCC = 4.5 V	I _{OL} = 64 mA			0.55*				0.55	V	
	B port	$V_{CC} = 4.5 \text{ V},$	I _{OL} = 12 mA			0.8		0.8		0.8	.	
V _{hys}					100						mV	
	Control inputs	$V_{CC} = 0 \text{ to } 5.5 \text{ V, } $	/I = V _{CC} or GND			±1		<i>‡</i> 1		±1		
l _l	A or B ports	V _{CC} = 2.1 V to 5.5 V, V _I = V _{CC} or GND				±20	±20			±20	μΑ	
lozpu	J	$V_{CC} = 0 \text{ to } 2.1 \text{ V},$ $V_{O} = 0.5 \text{ V to } 2.7 \text{ V}$	/, OE or OE = X§			±50	55	±50		±50	μА	
IOZPE)	V _{CC} = 2.1 V to 0, V _O = 0.5 V to 2.7 \	/, OE or OE = X§			±50	PAO	±50		±50	μА	
lozh‡	:	$V_{CC} = 2.1 \text{ V to } 5.5$ $V_{O} = 2.7 \text{ V, OE } \ge 2$				10		10		10	μА	
loz _L ‡		$V_{CC} = 2.1 \text{ V to } 5.5$ $V_{O} = 0.5 \text{ V, } \overline{OE} \ge 2$	V, ! V or OE ≤ 0.8 V			-10		-10		-10	μА	
l _{off}		$V_{CC} = 0$,	V_I or $V_O \le 4.5 V$			±100				±100	μΑ	
ICEX		V _{CC} = 5.5 V, V _O = 5.5 V	Outputs high			50		50		50	μА	
	A port			-50	-110	-180	-50	-180	-50	-180	,	
IO¶	B port	V _{CC} = 5.5 V,	$V_0 = 2.5 \text{ V}$	-25	-55	-90	-25	-90	-25	-90	mA	
		V _{CC} = 5.5 V,	Outputs high			3		3		3	mA	
Icc	A or B ports		Outputs low			36		36		36		
			Outputs disabled			3		3		3		
∆lcc#	1	V _{CC} = 5.5 V, One input at 3.4 V, Other inputs at V _{CC} or GND				50		50		50	μА	
Ci	Control inputs	V _I = 2.5 V or 0.5 V			3						pF	
C _{io}	A or B ports	V _O = 2.5 V or 0.5 \	/		9						pF	

^{*} On products compliant to MIL-PRF-38535, this parameter does not apply.



[†] All typical values are at $V_{CC} = 5 \text{ V}$.

[‡] The parameters I_{OZH} and I_{OZL} include the input leakage current.

[§] For V_{CC} between 2.1 V and 4 V, OE should be less than or equal to 0.5 V to ensure a low state.

[¶] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

[#]This is the increase in supply current for each input that is at the specified TTL voltage level rather than VCC or GND.

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timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

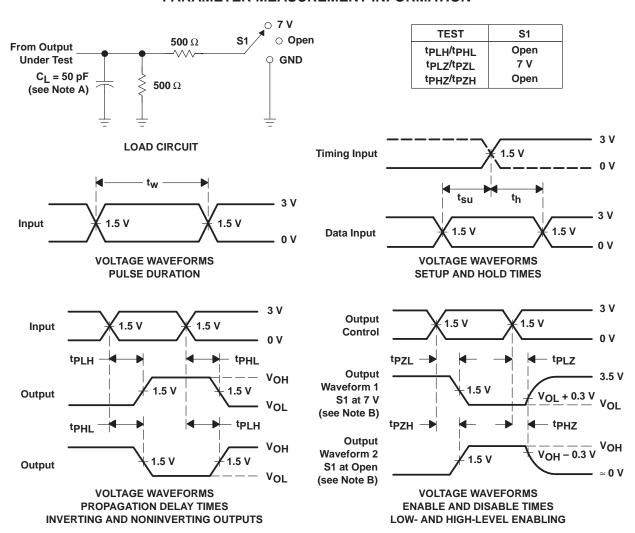
					162500	SN74ABT	UNIT	
				MIN	MAX	MIN	MAX	UNII
fclock	Clock frequency		150		150	MHz		
A Dulas duration		LEAB or LEBA high	LEAB or LEBA high			2.5		
t _W Pulse duration	CLKAB or CLKBA high or low	3	74	3		ns		
		A before CLKAB↓		3.3	A. A	3.3		
	Catum times	B before CLKBA↓		3.3	ζ	3.3		
t _{su}	Setup time	A before LEAB↓ or B before LEBA↓	CLK high	3		1		ns
	A belore LEAB\$\(\psi\) of B belore LEBA\$\(\psi\)	A before LEAB\$\(\text{ or B before LEBA}\) CLK low			2.5			
t _h Hold time	A after CLKAB↓ or B after CLKBA↓	A after CLKAB↓ or B after CLKBA↓			0		ns	
	A after LEAB↓ or B after LEBA↓		_	2		2		115

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)			V _{CC} = 5 V, T _A = 25°C		SN54ABT162500		SN74ABT162500		UNIT	
	(IIAF OT)	(001701)	MIN	TYP	MAX	MIN	MAX	MIN	MAX		
f _{max}			150	200		150		150		MHz	
t _{PLH}	A or B	B or A	1.5	2.6	4	1.5	5.1	1.5	4.8	ns	
t _{PHL}		BULK	2	3.4	5.2	2	6.1	2	5.7	115	
t _{PLH}	LEAB or LEBA	B or A	2	3.3	4.8	2	6.1	2	5.6	ns	
t _{PHL}	LEAD OF LEBA		2	3.8	5.2	2 2	6.4	2	5.9		
^t PLH	CLKAB or CLKBA	B or A	1.5	3.7	4.9	1.5	6.4	1.5	5.9	ns	
t _{PHL}	CLKAB OF CLKBA	BULK	1.5	3.8	5.2	1.5	6.4	1.5	6	115	
^t PZH	OEAB or OEBA	B or A	1.5	3.4	4.6	1.5	5.6	1.5	5.3	ns	
t _{PZL}	OEAB OF OEBA	B OL Y	2	3.8	4.7	2	5.6	2	5.4	115	
^t PHZ	OFAD OFDA	B or A	2	4.5	5.7	2	6.9	2	6.5		
tPLZ	OEAB or OEBA	D OF A	1.5	3.8	5.3	1.5	6.3	1.5	5.8	ns	

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PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_\Gamma \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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